

L Number	Hits	Search Text	DB	Time stamp
2	20	((bipolar adj transistor) and (base with ((silicon Si)and ((silicon adj germanium) sige si-ge)) same depletion)) not ((bipolar adj transistor) and (base with ((silicon Si)and ((silicon adj germanium) sige si-ge)) with depletion))	USPAT; US-PGPUB	2004/08/08 14:16
3	19	(bipolar adj transistor) and (base with ((silicon Si)and ((silicon adj germanium) sige si-ge)) with depletion)	USPAT; US-PGPUB	2004/08/08 13:34
4	39	((bipolar adj transistor) and (base with ((silicon Si)and ((silicon adj germanium) sige si-ge)) same depletion)) not ((bipolar adj transistor) and (base with ((silicon Si)and ((silicon adj germanium) sige si-ge)) with depletion))) or ((bipolar adj transistor) and (base with ((silicon Si)and ((silicon adj germanium) sige si-ge)) with depletion))	USPAT; US-PGPUB	2004/08/08 13:34
1	166	(bipolar adj transistor) and ((non-saturated nonsaturated ((non "not") adj saturated)))	USPAT; US-PGPUB	2004/08/08 14:32
5	33	((bipolar adj transistor) and ((non-saturated nonsaturated ((non "not") adj saturated)))) and (438/\$.ccls. or 257/\$.ccls.)	USPAT; US-PGPUB	2004/08/08 14:10
6	7	((bipolar adj transistor) and ((non-saturated nonsaturated ((non "not") adj saturated)))) and (438/\$.ccls. or 257/\$.ccls.) and (depletion)	USPAT; US-PGPUB	2004/08/08 13:59
7	2	("6762106") or ("5484737").PN.	USPAT; US-PGPUB	2004/08/08 14:10
8	0	((("6762106") or ("5484737")).PN.) and deplet\$	USPAT; US-PGPUB	2004/08/08 14:15
9	0	((("6762106") or ("5484737")).PN.) and breakdown	USPAT; US-PGPUB	2004/08/08 14:15
10	0	((("6762106") or ("5484737")).PN.) and boltage	USPAT; US-PGPUB	2004/08/08 14:15
11	1	((("6762106") or ("5484737")).PN.) and voltage	USPAT; US-PGPUB	2004/08/08 14:15
12	1	((("6762106") or ("5484737")).PN.) and voltage	USPAT; US-PGPUB	2004/08/08 14:15
13	192	((bipolar adj transistor) and (base with thickness with breakdown))	USPAT; US-PGPUB	2004/08/08 16:20
14	0	((bipolar adj transistor) and (base with thickness with breakdown))) not basis	USPAT; US-PGPUB	2004/08/08 14:32
15	0	((bipolar adj transistor) and (base with thickness with breakdown))) not "basis"	USPAT; US-PGPUB	2004/08/08 14:32
17	0	((bipolar adj transistor) and ((non-saturated nonsaturated ((non "not") adj saturated)))) and (((bipolar adj transistor) and (base with thickness with breakdown))) not "basis"	USPAT; US-PGPUB	2004/08/08 14:32
16	139	((bipolar adj transistor) and (base with thickness with breakdown))) not "basis"	USPAT; US-PGPUB	2004/08/08 16:19
18	42	((bipolar adj transistor) and (base with thickness with breakdown))) not "basis" and (thickness near2 base)	USPAT; US-PGPUB	2004/08/08 14:34
19	1	("5484737").PN.	USPAT; US-PGPUB	2004/08/08 15:24
20	0	("5484737").PN.) and (mis misfet)	USPAT; US-PGPUB	2004/08/08 15:24
21	0	("5484737").PN.) and (mis misfet)	USPAT; US-PGPUB	2004/08/08 15:30
22	1	("5484737").PN.) and (transistor)	USPAT; US-PGPUB	2004/08/08 15:24

23	0	((("5484737").PN.) and (heterojunction)	USPAT;	2004/08/08
			US-PGPUB	15:30
25	300	bipolar with mis	USPAT;	2004/08/08
			US-PGPUB	15:52
26	16	(bipolar with (misfet mis)) same	USPAT;	2004/08/08
		advantage	US-PGPUB	15:53
27	4	((bipolar adj transistor) and (base with	USPAT;	2004/08/08
		thickness with breakdown with optimiz\$))	US-PGPUB	16:22
28	7	((bipolar adj transistor) and (base with	USPAT;	2004/08/08
		thickness with optimiz\$) same breakdown)	US-PGPUB	16:29
29	5	((bipolar adj transistor) and (base with	USPAT;	2004/08/08
		thickness) same optimiz\$) same breakdown)	US-PGPUB	16:30
30	14	((bipolar adj transistor) and ((base with	USPAT;	2004/08/08
		thickness) same optimiz\$) same breakdown)	US-PGPUB	16:30
31	7	((bipolar adj transistor) and ((base	USPAT;	2004/08/08
		with thickness) same optimiz\$) same	US-PGPUB	16:31
		breakdown)) not ((bipolar adj		
		transistor) and (base with thickness with		
		optimiz\$) same breakdown))		
32	136	((((bipolar adj transistor) and (base	USPAT;	2004/08/08
		with thickness with breakdown))) not	US-PGPUB	16:33
		"basis") not (@ad>20030812 or		
		@rlad>20030812)		
33	128	((((bipolar adj transistor) and (base	USPAT;	2004/08/08
		with thickness with breakdown))) not	US-PGPUB	16:33
		"basis") not (@ad>20020815 or		
		@rlad>20020815)		
-	3	((("5323032") or ("5323031") or	USPAT;	2004/08/07
		("6365479")).PN.	US-PGPUB	14:24
-	34006	bipolar adj transistor	USPAT;	2004/08/07
			US-PGPUB	14:24
-	406	(bipolar adj transistor) and (base with	USPAT;	2004/08/07
		(silicon and (silicon adj germanium)))	US-PGPUB	18:33
-	92	(bipolar adj transistor) and (base with	USPAT;	2004/08/07
		(silicon and (silicon adj germanium))	US-PGPUB	18:41
		with (two second))		
-	102	(bipolar adj transistor) and (base with	USPAT;	2004/08/07
		(silicon and (silicon adj germanium))	US-PGPUB	18:13
		with (two second double stacked))		
-	177	(bipolar adj transistor) and (base with	USPAT;	2004/08/07
		(silicon and (silicon adj germanium) (si	US-PGPUB	15:30
		and sige)) with (two second double		
		stacked))		
-	82	(bipolar adj transistor) and (base with	USPAT;	2004/08/07
		("si/sige"))	US-PGPUB	15:56
-	8	(bipolar adj transistor) and (base with	USPAT;	2004/08/07
		("si/sige/si"))	US-PGPUB	16:06
-	1	("5798277").PN.	USPAT;	2004/08/07
			US-PGPUB	15:30
-	1	((("5798277").PN.) and emitter	USPAT;	2004/08/07
			US-PGPUB	15:31
-	84	(bipolar adj transistor) and (base with	USPAT;	2004/08/07
		("si/sige")) or (base with ("si/si-ge"))	US-PGPUB	15:57
-	82	((bipolar adj transistor) and (base with	USPAT;	2004/08/07
		("si/sige")) or (base with ("si/si-ge"))	US-PGPUB	19:04
		not (@ad>20030812 or @rlad>20030812)		
-	1	(bipolar adj transistor) and (base with	USPAT;	2004/08/07
		("si/si-ge/si"))	US-PGPUB	16:46
-	7	("5246316" "5389798" "5426316"	USPAT	2004/08/07
		"5440152" "5719415" "5798539"		16:27
		"6031256").PN.		
-	1	09/252908	USPAT;	2004/08/07
			US-PGPUB	16:46
-	98	((bipolar adj transistor) and (base with	USPAT;	2004/08/07
		(silicon and (silicon adj germanium))	US-PGPUB	17:07
		with (two second double stacked))) not		
		((bipolar adj transistor) and (base with		
		("si/sige")) or (base with ("si/si-ge"))		

-	97	((bipolar adj transistor) and (base with (silicon and (silicon adj germanium)) with (two second double stacked))) not ((bipolar adj transistor) and (base with ("si/sige")) or (base with ("si/si-ge")))) not (@ad>20030812 or @rlad>20030812)	USPAT; US-PGPUB	2004/08/08 16:33
-	1	("6346452").PN.	USPAT; US-PGPUB	2004/08/07 17:50
-	0	((("6346452").PN.) and emitter	USPAT; US-PGPUB	2004/08/07 17:50
-	1	10/638401	USPAT; US-PGPUB	2004/08/07 18:13
-	1	10/638401 and depletion	USPAT; US-PGPUB	2004/08/07 18:13
-	689	(bipolar adj transistor) and (base with ((silicon Si)and ((silicon adj germanium) sige si-ge)))	USPAT; US-PGPUB	2004/08/07 18:34
-	19	((bipolar adj transistor) and (base with ((silicon Si)and ((silicon adj germanium) sige si-ge)) with depletion)	USPAT; US-PGPUB	2004/08/08 13:34
-	39	(bipolar adj transistor) and (base with ((silicon Si)and ((silicon adj germanium) sige si-ge)) same depletion)	USPAT; US-PGPUB	2004/08/07 18:51
-	20	((bipolar adj transistor) and (base with ((silicon Si)and ((silicon adj germanium) sige si-ge)) same depletion)) not ((bipolar adj transistor) and (base with ((silicon Si)and ((silicon adj germanium) sige si-ge)) with depletion))	USPAT; US-PGPUB	2004/08/08 13:34
-	1	(bipolar adj transistor) and (base with ((silicon Si) and ((silicon adj germanium) sige si-ge)) same ((non-saturated nonsaturated ((non "not") adj saturated))))	USPAT; US-PGPUB	2004/08/08 13:33
-	75	((bipolar adj transistor) and (base with (silicon and (silicon adj germanium) (si and sige)) with (two second double stacked))) not ((bipolar adj transistor) and (base with (silicon and (silicon adj germanium)) with (two second double stacked)))	USPAT; US-PGPUB	2004/08/07 19:04
-	73	((bipolar adj transistor) and (base with (silicon and (silicon adj germanium) (si and sige)) with (two second double stacked))) not ((bipolar adj transistor) and (base with (silicon and (silicon adj germanium)) with (two second double stacked))) not (@ad>20030812 or @rlad>20030812)	USPAT; US-PGPUB	2004/08/07 19:04
-	51	((bipolar adj transistor) and (base with (silicon and (silicon adj germanium) (si and sige)) with (two second double stacked))) not ((bipolar adj transistor) and (base with (silicon and (silicon adj germanium)) with (two second double stacked))) not (@ad>20030812 or @rlad>20030812) not (((bipolar adj transistor) and (base with ("si/sige")) or (base with ("si/si-ge")))) not (@ad>20030812 or @rlad>20030812))	USPAT; US-PGPUB	2004/08/07 19:04

-	51	(((bipolar adj transistor) and (base with (silicon and (silicon adj germanium) (si and sige)) with (two second double stacked))) not ((bipolar adj transistor) and (base with (silicon and (silicon adj germanium)) with (two second double stacked))) not (@ad>20030812 or @rlad>20030812)) not (((bipolar adj transistor) and (base with ("si/sige")) or (base with ("si/si-ge")))) not (@ad>20030812 or @rlad>20030812))) not ((bipolar adj transistor) and (base with ("si/sige/si")))	USPAT; US-PGPUB	2004/08/07 19:11
-	3	hirofumi near kawai	USPAT; US-PGPUB	2004/08/07 19:11